

1. Record Nr.	UNICASIEI0031148
Autore	Dulles, Foster Rhea
Titolo	Storia del movimento operaio americano / Foster Rhea Dulles
Pubbl/distr/stampa	Milano, : Edizioni di Comunità, 1953
Titolo uniforme	Labor in America: a history
Descrizione fisica	XXIV, 372 p. ; 25 cm
Disciplina	331.8097309034
Soggetti	Movimento operaio - Stati Uniti d'America Sindacalismo - Stati Uniti d'America Movimento operaio - Stati Uniti d'America - Sec. 19.-20
Lingua di pubblicazione	Italiano
Formato	Materiale a stampa
Livello bibliografico	Monografia
Note generali	Traduzione e note di Pino Tagliazucchi.

2. Record Nr.	UNINA9910143501403321
Titolo	Approximation algorithms for combinatorial optimization : international workshop, APPROX '98, Aalborg, Denmark, July 18-19, 1998 : proceedings / / Klaus Jansen, Jose Rolim (eds.)
Pubbl/distr/stampa	Springer Berlin / Heidelberg
Altri autori (Persone)	RolimJosé D. P JansenKlaus
Disciplina	005.1
Soggetti	Computer algorithms Approximation theory - Data processing - Congresses Combinatorial optimization - Data processing - Congresses
Lingua di pubblicazione	Inglese
Formato	Materiale a stampa
Livello bibliografico	Monografia

3. Record Nr.	UNINA9910958087303321
Autore	Baliga B. Jayant <1948->
Titolo	Silicon carbide power devices / / B. Jayant Baliga
Pubbl/distr/stampa	New Jersey, : World Scientific, c2005
ISBN	9789812774521 9812774521
Edizione	[1st ed.]
Descrizione fisica	1 online resource (xxi, 503 p.) : ill. (some col.)
Disciplina	621.3815/2
Soggetti	Silicon carbide - Electric properties Semiconductors
Lingua di pubblicazione	Inglese
Formato	Materiale a stampa
Livello bibliografico	Monografia
Note generali	Bibliographic Level Mode of Issuance: Monograph
Nota di bibliografia	Includes bibliographical references and index.
Nota di contenuto	ch. 1. Introduction -- ch. 2. Material properties and technology -- ch. 3. Breakdown voltage -- ch. 4. PiN rectifiers -- ch. 5. Schottky rectifiers -- ch. 6. Shielded Schottky rectifiers -- ch. 7. Metal-semiconductor field effect transistors -- ch. 8. The Baliga-pair configuration -- ch. 9. Planar power MOSFETs -- ch. 10. Shielded planar MOSFETs -- ch. 11. Trench-gate power MOSFETs -- ch. 12. Shielded trench-gate power MOSFETs -- ch. 13. Charge coupled structures -- ch. 14. Integral diodes -- ch. 15. Lateral high voltage FETs -- ch. 16. Synopsis.
Sommario/riassunto	Power semiconductor devices are widely used for the control and management of electrical energy. The improving performance of power devices has enabled cost reductions and efficiency increases resulting in lower fossil fuel usage and less environmental pollution. This book provides the first cohesive treatment of the physics and design of silicon carbide power devices with an emphasis on unipolar structures. It uses the results of extensive numerical simulations to elucidate the operating principles of these important devices. Sample Chapter(s). Chapter 1: Introduction (72 KB). Contents: Material Properties and Technology; Breakdown Voltage; PiN Rectifiers; Schottky Rectifiers; Shielded Schottky Rectifiers; Metal-Semiconductor Field Effect Transistors; The Baliga-Pair Configuration; Planar Power MOSFETs; Shielded Planar MOSFETs; Trench-Gate Power MOSFETs; Shielded Trendch-Gate MOSFETs; Charge Coupled Structures; Integral Diodes;

Lateral High Voltage FETs; Synopsis. Readership: For practising engineers working on power devices, and as a supplementary textbook for a graduate level course on power devices.
